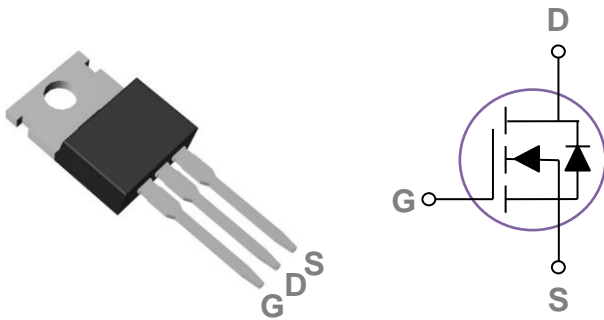


100V N-Channel MOSFETs

General Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

TO220 Pin Configuration



BVDSS	RDSON	ID
100V	38mΩ	25A

Features

- 100V,25A, RDS(ON) =38mΩ @VGS = 10V
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

Applications

- Networking
- Load Switch
- LED applications

Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	+20 / -12	V
I_D	Drain Current – Continuous ($T_c=25^\circ\text{C}$)	25	A
	Drain Current – Continuous ($T_c=100^\circ\text{C}$)	16	A
I_{DM}	Drain Current – Pulsed ¹	100	A
EAS	Single Pulse Avalanche Energy ²	34	mJ
IAS	Single Pulse Avalanche Current ²	26	A
P_D	Power Dissipation ($T_c=25^\circ\text{C}$)	64	W
	Power Dissipation – Derate above 25°C	0.51	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	1.96	$^\circ\text{C}/\text{W}$



100V N-Channel MOSFETs

Electrical Characteristics ($T_J=25\text{ }^\circ\text{C}$, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	100	---	---	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=100V$, $V_{GS}=0V$, $T_J=25\text{ }^\circ\text{C}$	---	---	1	μA
		$V_{DS}=80V$, $V_{GS}=0V$, $T_J=85\text{ }^\circ\text{C}$	---	---	10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=20V$, $V_{DS}=0V$	---	---	100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance ³	$V_{GS}=10V$, $I_D=10A$	---	32	38	m Ω
		$V_{GS}=4.5V$, $I_D=8A$	---	48	62	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1.0	1.6	2.5	V
g_{fs}	Forward Transconductance	$V_{DS}=10V$, $I_D=3A$	---	8	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge ^{3, 4}	$V_{DS}=50V$, $V_{GS}=10V$, $I_D=15A$	---	8.7	15	nC
Q_{gs}	Gate-Source Charge ^{3, 4}		---	1.1	3	
Q_{gd}	Gate-Drain Charge ^{3, 4}		---	3.5	6	
$T_{d(on)}$	Turn-On Delay Time ^{3, 4}	$V_{DD}=50V$, $V_{GS}=10V$, $R_G=6\Omega$ $I_D=15A$	---	8	15	ns
T_r	Rise Time ^{3, 4}		---	12	20	
$T_{d(off)}$	Turn-Off Delay Time ^{3, 4}		---	25	40	
T_f	Fall Time ^{3, 4}		---	18	30	
C_{iss}	Input Capacitance	$V_{DS}=50V$, $V_{GS}=0V$, $F=1\text{MHz}$	---	550	825	pF
C_{oss}	Output Capacitance		---	100	150	
C_{rss}	Reverse Transfer Capacitance		---	6	10	
R_g	Gate Resistance	$V_{GS}=0V$, $V_{DS}=0V$, $F=1\text{MHz}$	---	0.8	---	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	25	A
I_{SM}	Pulsed Source Current		---	---	50	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=1A$, $T_J=25\text{ }^\circ\text{C}$	---	---	1	V
t_{rr}	Reverse Recovery Time ³	$V_R=100V$, $I_S=10A$, $di/dt=100A/\mu s$, $T_J=25\text{ }^\circ\text{C}$	---	45	---	ns
Q_{rr}	Reverse Recovery Charge ³		---	50	---	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. $V_{DD}=50V$, $V_{GS}=10V$, $L=0.1\text{mH}$, $I_{AS}=26A$, $R_G=25\Omega$, Starting $T_J=25\text{ }^\circ\text{C}$.
3. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. Essentially independent of operating temperature.

100V N-Channel MOSFETs

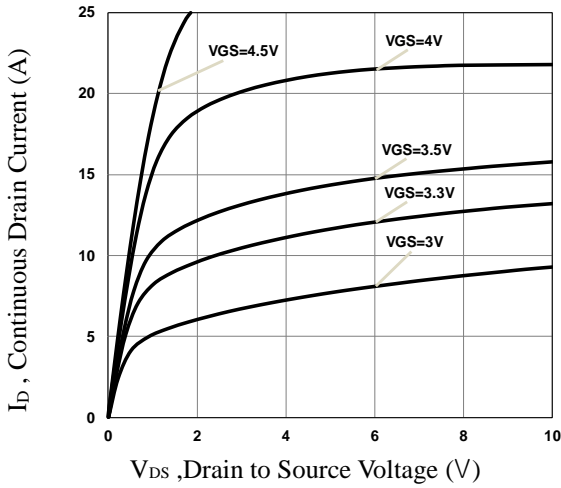


Fig.1 Typical Output Characteristics

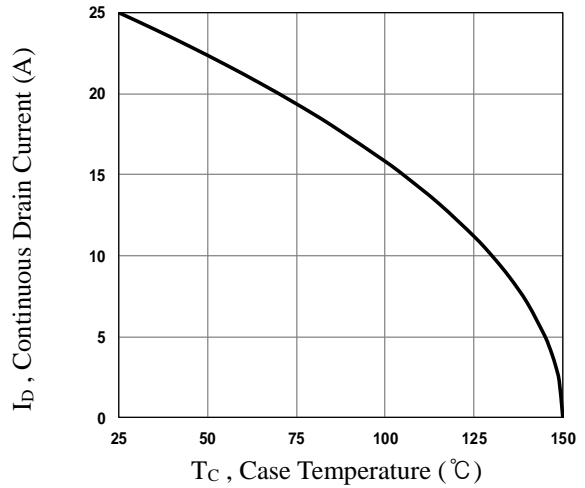


Fig.2 Continuous Drain Current vs. T_c

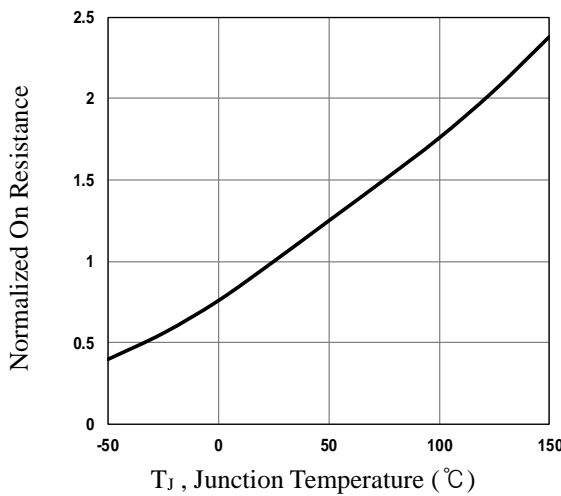


Fig.3 Normalized $R_{DS(on)}$ vs. T_J

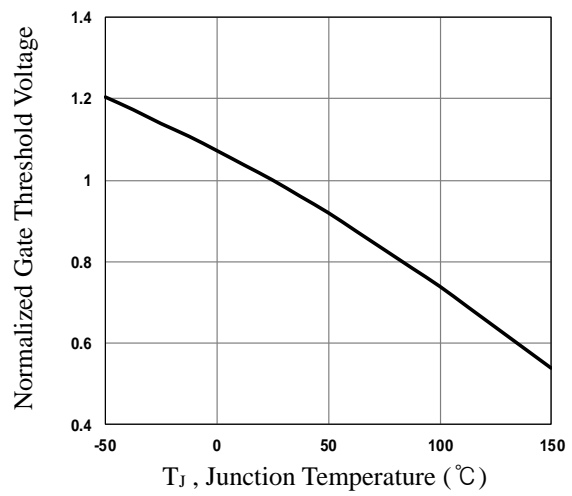


Fig.4 Normalized V_{th} vs. T_J

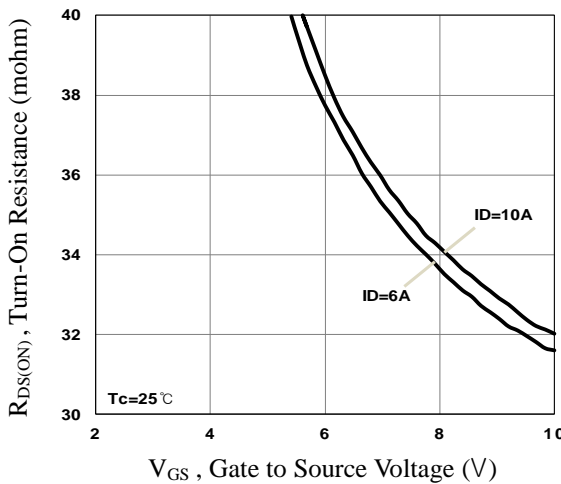


Fig.5 Turn-On Resistance vs. V_{GS}

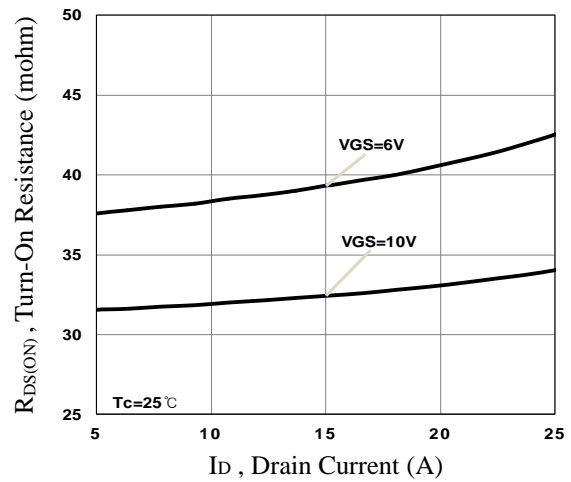


Fig.6 Turn-On Resistance vs. I_D

100V N-Channel MOSFETs

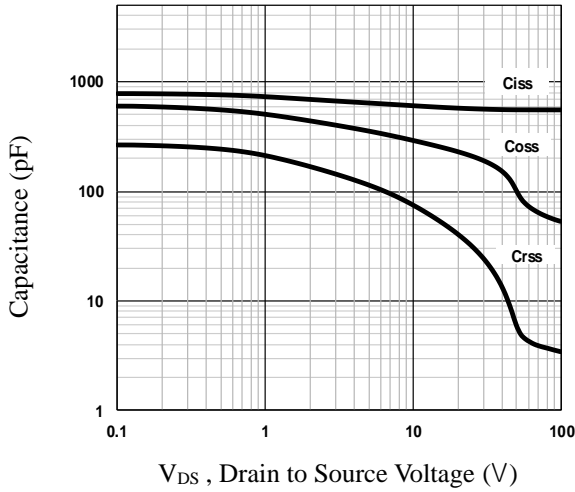


Fig.7 Capacitance Characteristics

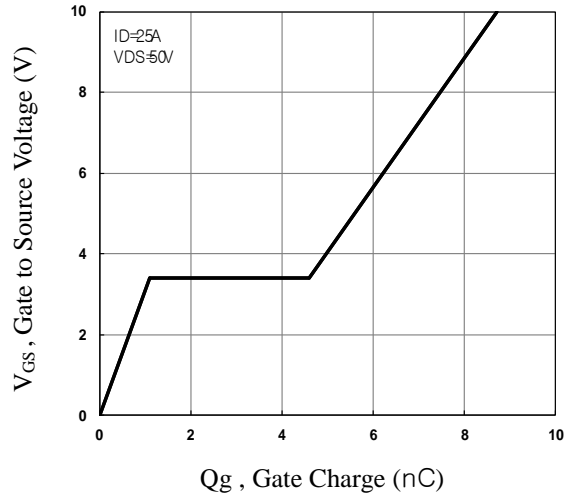


Fig.8 Gate Charge Characteristics

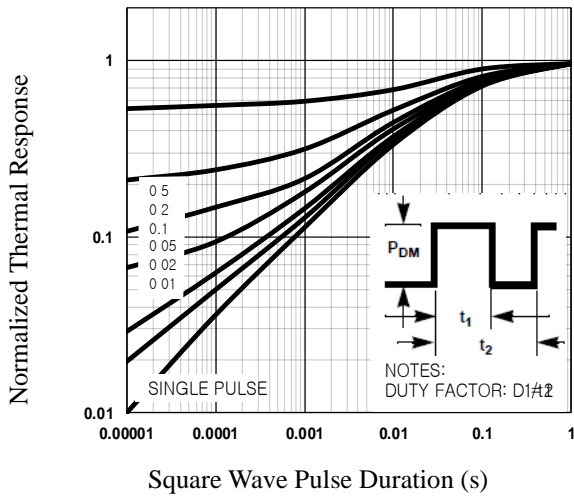


Fig.9 Normalized Transient Impedance

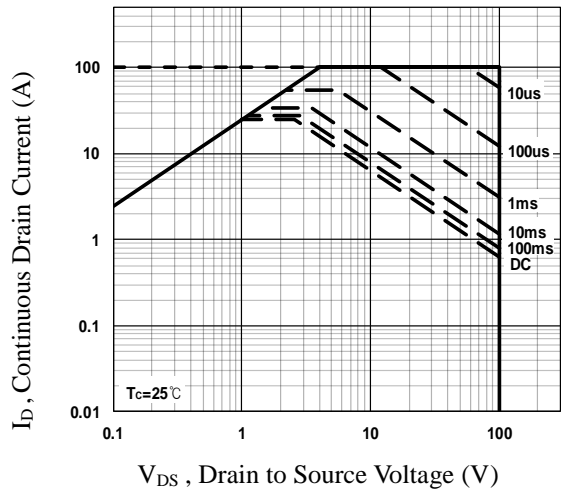


Fig.10 Maximum Safe Operation Area

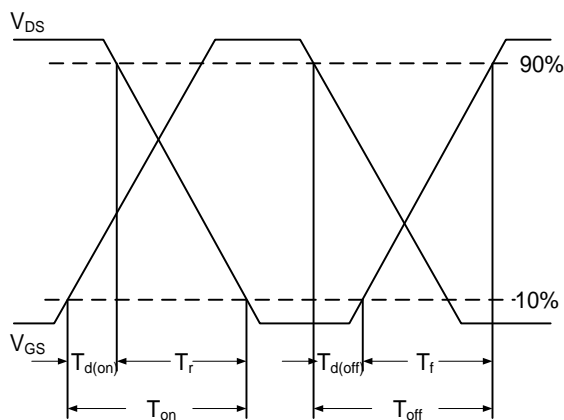


Fig.11 Switching Time Waveform

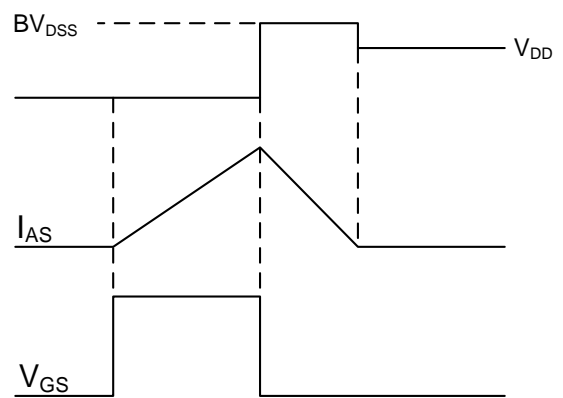
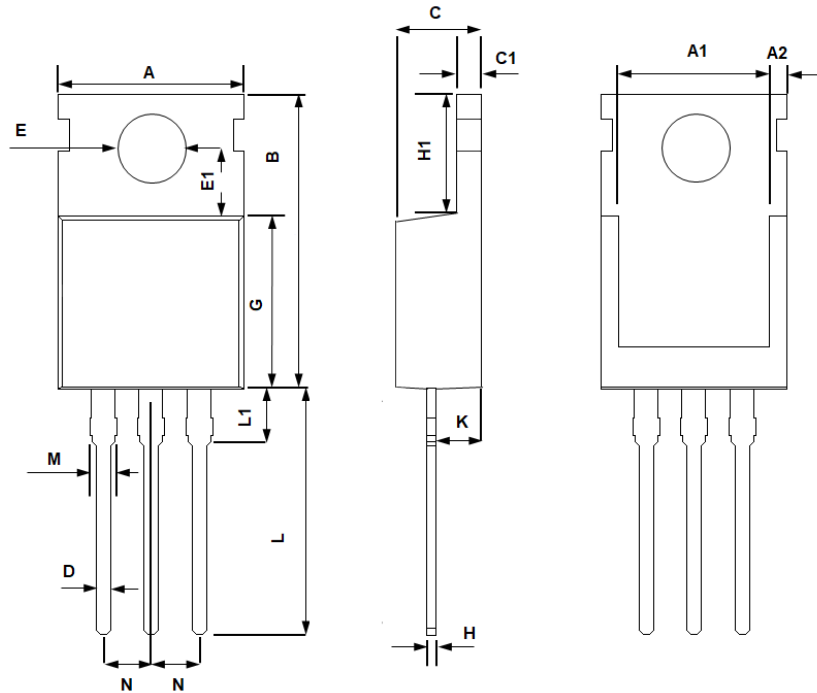


Fig.12 EAS Waveform

100V N-Channel MOSFETs
TO220 PACKAGE INFORMATION


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	10.400	9.700	0.409	0.382
A1	8.900	7.400	0.350	0.291
A2	1.400	0.800	0.055	0.031
B	16.500	14.500	0.650	0.571
C	4.750	4.200	0.187	0.165
C1	1.500	1.100	0.059	0.043
D	1.000	0.600	0.039	0.024
E	4.000	3.300	0.157	0.130
E1	3.800	3.400	0.150	0.134
G	9.400	8.400	0.370	0.331
H	0.600	0.200	0.024	0.008
H1	6.850	6.200	0.270	0.244
K	2.850	2.100	0.112	0.083
L	14.000	12.500	0.551	0.492
L1	4.000	2.700	0.157	0.106
M	1.750	1.100	0.069	0.043
N	2.640	2.440	0.104	0.096